

BUX98 BUX98A

HIGH POWER NPN SILICON TRANSISTORS

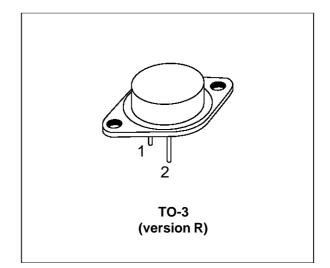
- SGS-THOMSON PREFERRED SALESTYPES
- NPN TRANSISTOR
- HIGH VOLTAGE CAPABILITY
- HIGH CURRENT CAPABILITY
- FAST SWITCHING SPEED

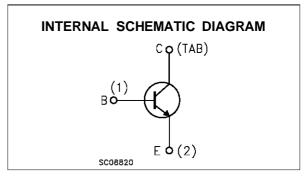
APPLICATIONS

- HIGH FREQUENCY AND EFFICENCY CONVERTERS
- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

DESCRIPTION

The BUX98 and BUX98A are silicon multiepitaxial mesa NPN transistor in jedec TO-3 metal case, intended and industrial applications from single and three-phase mains operation.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Va	Unit		
		BUX98	BUX98A	7	
V _{CER}	Collector-Emitter Voltage (RBE = $\leq 10 \Omega$)	850	1000	V	
VCES	Collector-Base Voltage (V _{BE} = 0)	llector-Base Voltage (V _{BE} = 0) 850 1000			
V _{CEO}	Collector-Emitter Voltage (IB = 0)	400 450		V	
V _{EBO}	Emitter-Base Voltage (IC = 0)		V		
Ι _C	Collector Current	30		A	
I _{CM}	Collector Peak Current (tp < 5 ms)	60		A	
ICP	Collector Peak Current non Rep. (tp < 20 µs)	Current non Rep. (tp < 20 μs) 80		A	
Ι _Β	Base Current 8		8	A	
I _{BM}	ase Peak Current (t _p < 5 ms) 30		A		
Ptot	Total Power Dissipation at T _{case} < 25 °C	250		W	
T _{stg}	Storage Temperature	-65 to 200		°C	
Tj	Max Operating Junction Temperature	2	200		

THERMAL DATA

R _{thj-case} Thermal Resistance Junction-case	Мах	0.7	°C/W
--	-----	-----	------

ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \,^{\circ}C$ unless otherwise specified)

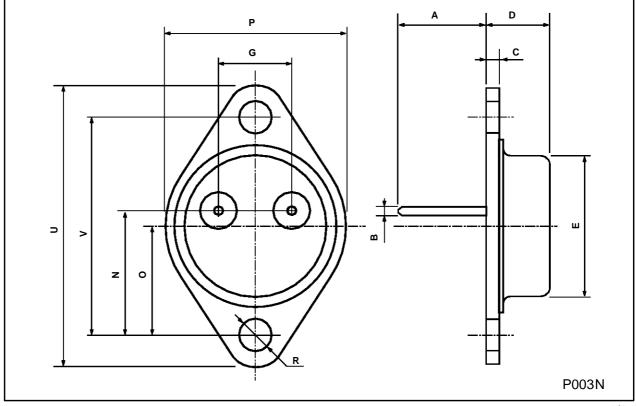
Symbol	Parameter Test Conditions			Min.	Тур.	Max.	Unit
I _{CER}	Collector Cut-off Current ($R_{BE} = 10 \Omega$)	V _{CE} = V _{CES} V _{CE} = V _{CES}	T _{CASE} = 125 °C			1 8	μA mA
I _{CES}	Collector Cut-off Current ($V_{BE} = 0$)	V _{CE} = V _{CES} V _{CE} = V _{CES}	T _{CASE} = 125 °C			400 4	μA mA
I _{CEO}	Collector Cut-off Current ($I_B = 0$)	V _{CE} = V _{CEO}				2	mA
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	V _{EB} = 5 V				2	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage	Ic = 200 mA for BUX98 for BUX98A		400 450			V V
$V_{CER(sus)}*$	Collector-Emitter Sustaining Voltage	L = 2mH for BUX98 for BUX98A	Ic = 1 A	850 1000			V V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	for BUX98 I _C = 20 A for BUX98A I _C = 16 A I _C = 24 A	I _B = 4 A I _B = 3.2 A I _B = 5 A			1.5 1.5 5	V V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	for BUX98 I _C = 20 A for BUX98A I _C = 16 A	I _B = 4 A I _B = 3.2 A			1.6 1.6	V V
t _{on}	Turn-on Time	for BUX98				1	μs
ts	Storage Time	V _{CC} = 150 V	I _C = 20 A			3	μs
t _f	Fall Time	I _{B1} = - I _{B2} = 4 A				0.8	μs
ton	Turn-on Time	for BUX98A				1	μs
ts	Storage Time	V _{CC} = 150 V	$I_{\rm C} = 16 {\rm A}$			3	μs
t _f	Fall Time	I _{B1} = - I _{B2} = 3.2 A				0.8	μs

* Pulsed: Pulse duration = 300 μs, duty cycle = 1.5 %



DIM.	mm			inch			
Dim	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А		11.7			0.460		
В	0.96		1.10	0.037		0.043	
С			1.70			0.066	
D			8.7			0.342	
E			20.0			0.787	
G		10.9			0.429		
Ν		16.9			0.665		
Р			26.2			1.031	
R	3.88		4.09	0.152		0.161	
U			39.50			1.555	
V		30.10			1.185		





SGS-THOMSON MICROELECTRONICS

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsability for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may results from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectonics.

© 1997 SGS-THOMSON Microelectronics - Printed in Italy - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES Australia - Brazil - Canada - China - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A

